# RENESAS

# R1WV6416R Series

64Mb Advanced LPSRAM (4M word x 16bit / 8M word x 8bit)

REJ03C0368-0100 Rev.1.00 2009.05.07

#### Description

The R1WV6416R Series is a family of low voltage 64-Mbit static RAMs organized as 4,194,304-word by 16-bit, fabricated by Renesas's high-performance 0.15um CMOS and TFT technologies.

The R1WV6416R Series is suitable for memory applications where a simple interfacing, battery operating and battery backup are the important design objectives.

The R1WV6416R Series is provided in 48-pin thin small outline package [TSOP (I): 12mm x 20mm with pin pitch of 0.5mm], 52-pin micro thin small outline package [µTSOP (II): 10.79mm x 10.49mm with pin pitch of 0.4mm] and 48-ball fine pitch ball grid array [f-BGA] package. It gives the best solution for compaction of mounting area as well as flexibility of wiring pattern of printed circuit boards.

#### Features

- Single 2.7~3.6V power supply
- Small stand-by current: 8 µA (3.0V, typical)
- No clocks, No refresh
- All inputs and outputs are TTL compatible.
- Easy memory expansion by CS1#, CS2, LB# and UB#
- Common Data I/O
- Three-state outputs: OR-tie Capability
- OE# prevents data contention on the I/O bus

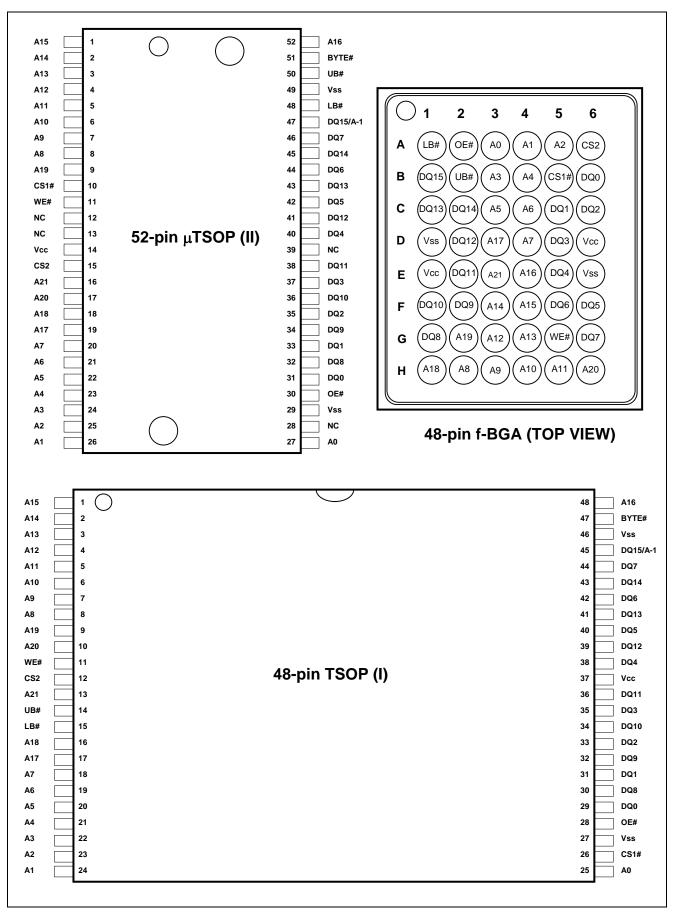
Type No.	Access time	Package
R1WV6416RSA-5S%	55 ns	12mm x 20mm 48-pin plastic TSOP (I)
R1WV6416RSA-7S%	70 ns	(normal-bend type) (48P3R)
R1WV6416RSD-5S%	55 ns	350 mil 52-pin plastic μ-TSOP (II)
R1WV6416RSD-7S%	70 ns	(normal-bend type) (52PTG)
R1WV6416RBG-5S%	55 ns	f DCA 0.75mm nitch 49 holl
R1WV6416RBG-7S%	70 ns	f-BGA 0.75mm pitch 48-ball

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%	Temperature Range						
R	0 ~ +70 °C						
I	-40 ~ +85 °C						



#### **Pin Arrangement**



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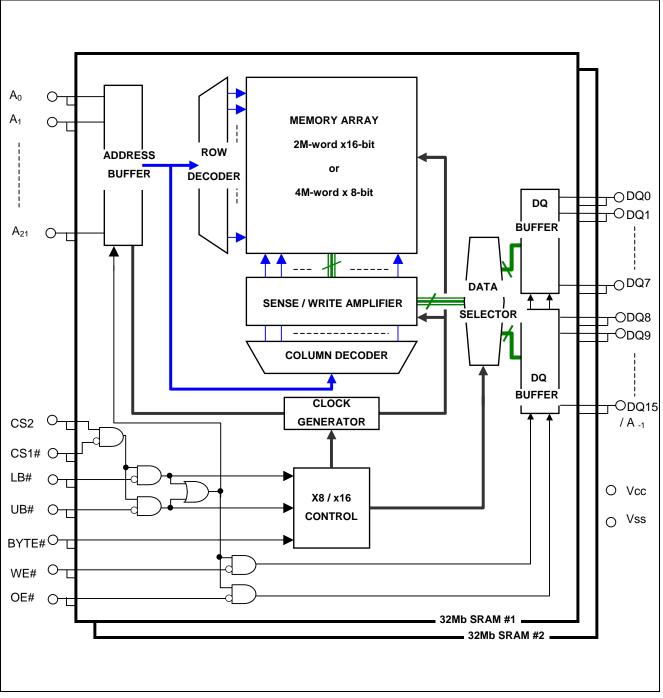
## Pin Description

Pin name	Function
Vcc	Power supply
Vss	Ground
A0 to A21	Address input (word mode)
A-1 to A21	Address input (byte mode)
DQ0 to DQ15	Data input/output
CS1#	Chip select 1
CS2	Chip select 2
WE#	Write enable
OE#	Output enable
LB#	Lower byte enable
UB#	Upper byte enable
BYTE#	Byte control mode enable
NC	Non connection

Note: BYTE# pin is supported for 48-pin TSOP (I) and 52-pin  $\mu$ TSOP (II) packages.



### Block Diagram



Note: BYTE# pin is supported for 48-pin TSOP (I) and 52-pin  $\mu$ TSOP (II) packages.



### **Operation Table**

CS1#	CS2	BYTE#	LB#	UB#	WE#	OE#	DQ0~7	DQ8~14	DQ15	Operation
Н	Х	Х	Х	Х	Х	Х	High-Z	High-Z	High-Z	Stand-by
Х	L	Х	Х	Х	Х	Х	High-Z	High-Z	High-Z	Stand-by
Х	Х	Н	Н	Н	Х	Х	High-Z	High-Z	High-Z	Stand-by
L	Н	Н	L	H	L	Х	Din	High-Z	High-Z	Write in lower byte
L	Н	Н	L	Н	Н	L	Dout	High-Z	High-Z	Read in lower byte
L	Н	Н	L	H	Н	Н	High-Z	High-Z	High-Z	Output disable
L	Н	Н	Н	L	L	Х	High-Z	Din	Din	Write in upper byte
L	Н	Н	Н	L	Н	L	High-Z	Dout	Dout	Read in upper byte
L	Н	Н	Н	L	Н	Н	High-Z	High-Z	High-Z	Output disable
L	Н	Н	L	L	L	Х	Din	Din	Din	Word write
L	Н	Н	L	L	Н	L	Dout	Dout	Dout	Word read
L	Н	Н	L	L	Н	Н	High-Z	High-Z	High-Z	Output disable
L	Н	L	L	L	L	Х	Din	High-Z	A-1	Byte write
L	Н	L	L	L	Н	L	Dout	High-Z	A-1	Byte read
L	Н	L	L	L	Н	Н	High-Z	High-Z	A-1	Output disable

Note1. H:  $V_{IH} \quad L{:}V_{IL} \quad X{:}\;V_{IH} \text{ or }V_{IL}$ 

2. BYTE# pin is supported for 48-pin TSOP (I) and 52-pin  $\mu\text{TSOP}$  (II) packages.

3. When apply BYTE# ="L", please assign LB#=UB#="L".

#### Absolute Maximum Ratings

Parameter	Symbol		Value	unit	
Power supply voltage relative to Vss	Vcc		-0.5 to +4.6	V	
Terminal voltage on any pin relative to Vss	VT		-0.5 <sup>*1</sup> to Vcc+0.3 <sup>*2</sup> V		
Power dissipation	PT		0.7	W	
	Topr <sup>*3</sup>	R ver.	0 to +70	°C	
Operation temperature	горг	l ver.	-40 to +85	°C	
Storage temperature range	Tstg		-65 to 150	°C	
Ctorage temperature range under bigs	Tbias <sup>*3</sup>	R ver.	0 to +70	°C	
Storage temperature range under bias	TUIAS	l ver.	-40 to +85	°C	

Note 1. –2.0V in case of AC (Pulse width ≤30ns)

2. Maximum voltage is +4.6V.

3. Ambient temperature range depends on R/I-version. Please see table on page 1.



### **Recommended Operating Conditions**

Parameter		Symbol	Min.	Тур.	Max.	Unit	Note
Supply voltage		Vcc	2.7	3.0	3.6	V	
		Vss	0	0	0	V	
Input high voltage	Input high voltage		2.4	-	Vcc+0.2	V	
Input low voltage	Input low voltage		-0.2	-	0.4	V	1
Ambient temperature range	R ver.	Та	0	-	+70	°C	2
	I ver.	ia	-40	-	+85	°C	2

Note 1. –2.0V in case of AC (Pulse width  $\leq$  30ns)

2. Ambient temperature range depends on R/I-version. Please see table on page 1.

### **DC** Characteristics

Parameter	Symbol	Min.	Тур.	Max.	Unit		Test conditions <sup>*3</sup>		
Input leakage current	I <sub>LI</sub>	-	-	1	μA	Vin = Vss to Vcc			
Output leakage current	I <sub>LO</sub>	-	-	1	μΑ	$\begin{split} & \text{BYTE} \# \geq \text{Vcc -}0.2\text{V or BYTE} \# \leq 0.2\text{V} \\ & \text{CS1} \# = \text{V}_{\text{IH}} \text{ or CS2 } = \text{V}_{\text{IL}} \text{ or} \\ & \text{OE} \# = \text{V}_{\text{IH}} \text{ or WE} \# = \text{V}_{\text{IL}} \text{ or} \\ & \text{LB} \# = \text{UB} \# = \text{V}_{\text{IH}}, \text{ VI/O } = \text{Vss to Vcc} \end{split}$			
Average operating current	I <sub>CC1</sub>	-	45 <sup>*1</sup>	60	mA	BYTE# ≥	e, duty =100%, II/O = 0mA Vcc -0.2V or BYTE# ≤ 0.2V <sub>IL</sub> , CS2 =V <sub>IH</sub> , Others = V <sub>IH</sub> /V <sub>IL</sub>		
	I <sub>CC2</sub>	-	5 <sup>*1</sup>	10	mA	BYTE# ≥ CS1# ≤ 0	µs, duty =100%, II/O = 0mA Vcc -0.2V or BYTE# ≤ 0.2V 0.2V, CS2 ≥ V <sub>CC</sub> -0.2V, -0.2V, V <sub>IL</sub> ≤ 0.2V		
Standby current	I <sub>SB</sub>	-	0.1 <sup>*1</sup>	0.3	mA	BYTE# ≥ CS2 =V <sub>IL</sub>	Vcc -0.2V or BYTE# ≤ 0.2V		
Standby current		-	8 <sup>*1</sup>	24	μA	~+25°C	Vin ≥ 0V BYTE# ≥ Vcc -0.2V or		
		-	14 <sup>*2</sup>	48	μΑ	~+40°C	BYTE# $\leq 0.2V$ (1) 0V $\leq CS2 \leq 0.2V$ or (2) CS4# $\geq V$ = 0.2V		
	I <sub>SB1</sub>	-	-	100	μA	~+70°C	(2) CS1# $\geq$ V <sub>CC</sub> -0.2V, CS2 $\geq$ V <sub>CC</sub> -0.2V or (3) LB# = UB# $\geq$ V <sub>CC</sub> -0.2V,		
		-	-	160	μA	~+85°C	$CS1\# \le 0.2V,$ $CS2 \ge V_{CC}-0.2V$		
Output high voltage	V <sub>OH</sub>	2.4	-	-	V	BYTE# ≥ Vcc -0.2V or BYTE# ≤ 0.2V I <sub>OH</sub> = -0.5mA			
Output low voltage	V <sub>OL</sub>	-	-	0.4	V	-	Vcc -0.2V or BYTE# ≤ 0.2V		

Note 1. Typical parameter indicates the value for the center of distribution at 3.0V (Ta= 25°C), and not 100% tested.

2. Typical parameter indicates the value for the center of distribution at 3.0V (Ta=  $40^{\circ}$ C), and not 100% tested.

3. BYTE# pin is supported for 48-pin TSOP (I) and 52-pin  $\mu\text{TSOP}$  (II) packages.



#### Capacitance

(Ta =25°C, f =1MHz)

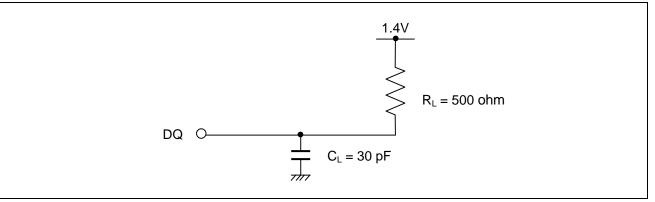
						( )	/
Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions	Note
Input capacitance	C in	-	-	20	pF	Vin =0V	1
Input / output capacitance	C I/O	-	-	20	pF	V <sub>I/O</sub> =0V	1
1	- 1/0			_		1/8 ·	

Note1.This parameter is sampled and not 100% tested.

#### **AC Characteristics**

Test Conditions (Vcc =  $2.7V \sim 3.6V$ , Ta =  $0 \sim +70^{\circ}C / -40 \sim +85^{\circ}C^{*1}$ )

- Input pulse levels:  $V_{IL} = 0.4V$ ,  $V_{IH} = 2.4V$
- Input rise and fall time: 5ns
- Input and output timing reference level: 1.4V
- Output load: See figures (Including scope and jig)



Note1. Ambient temperature range depends on R/I-version. Please see table on page 1.





### Read Cycle

Parameter	Symbol	R1WV64	16R**-5S	R1WV64	16R**-7S	Unit	Note
Falameter	Symbol	Min.	Max.	Min.	Max.	Onit	NOLE
Read cycle time	t <sub>RC</sub>	55	-	70	-	ns	
Address access time	t <sub>AA</sub>	-	55	-	70	ns	
Chip coloct copped time	t <sub>ACS1</sub>	-	55	-	70	ns	
Chip select access time	t <sub>ACS2</sub>	-	55	-	70	ns	
Output enable to output valid	t <sub>OE</sub>	-	25	-	35	ns	
Output hold from address change	t <sub>OH</sub>	10	-	10	-	ns	
LB#, UB# access time	t <sub>BA</sub>	-	55	-	70	ns	
Chip poloot to output in low 7	t <sub>CLZ1</sub>	10	-	10	-	ns	2,3
Chip select to output in low-Z	t <sub>CLZ2</sub>	10	-	10	-	ns	2,3
LB#, UB# enable to low-Z	t <sub>BLZ</sub>	5	-	5	-	ns	2,3
Output enable to output in low-Z	t <sub>OLZ</sub>	5	-	5	-	ns	2,3
Chip decoloring output in high 7	t <sub>CHZ1</sub>	0	20	0	25	ns	1,2,3
Chip deselect to output in high-Z	t <sub>CHZ2</sub>	0	20	0	25	ns	1,2,3
LB#, UB# disable to high-Z	t <sub>BHZ</sub>	0	20	0	25	ns	1,2,3
Output disable to output in high-Z	t <sub>OHZ</sub>	0	20	0	25	ns	1,2,3



#### Write Cycle

Parameter	Symbol	R1WV6416R**-5S		R1WV64	16R**-7S	Unit	Note
Falameter	Symbol	Min.	Max.	Min.	Max.	Offic	NOLE
Write cycle time	t <sub>WC</sub>	55	-	70	-	ns	
Address valid to end of write	t <sub>AW</sub>	50	-	65	-	ns	
Chip select to end of write	t <sub>CW</sub>	50	-	65	-	ns	5
Write pulse width	t <sub>WP</sub>	40	-	55	-	ns	4
LB#, UB# valid to end of write	t <sub>BW</sub>	50	-	65	-	ns	
Address setup time	t <sub>AS</sub>	0	-	0	-	ns	6
Write recovery time	t <sub>WR</sub>	0	-	0	-	ns	7
Data to write time overlap	t <sub>DW</sub>	25	-	35	-	ns	
Data hold from write time	t <sub>DH</sub>	0	-	0	-	ns	
Output enable from end of write	tow	5	-	5	-	ns	2
Output disable to output in high-Z	t <sub>OHZ</sub>	0	20	0	25	ns	1,2
Write to output in high-Z	t <sub>WHZ</sub>	0	20	0	25	ns	1,2

Note1. t<sub>CHZ</sub>, t<sub>OHZ</sub>, t<sub>WHZ</sub> and t<sub>BHZ</sub> are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.

2. This parameter is sampled and not 100% tested.

3. At any given temperature and voltage condition,  $t_{HZ}$  max is less than  $t_{LZ}$  min both for a given device and from device to device.

4. A write occurs during the overlap of a low CS1#, a high CS2, a low WE# and a low LB# or a low UB#.

A write begins at the latest transition among CS1# going low, CS2 going high, WE# going low and LB# going low or UB# going low .

A write ends at the earliest transition among CS1# going high, CS2 going low, WE# going high and LB# going high or UB# going high. t<sub>WP</sub> is measured from the beginning of write to the end of write.

5.  $t_{CW}$  is measured from the later of CS1# going low or CS2 going high to end of write.

6.  $t_{\text{AS}}$  is measured the address valid to the beginning of write.

7. t<sub>WR</sub> is measured from the earliest of CS1# or WE# going high or CS2 going low to the end of write cycle.

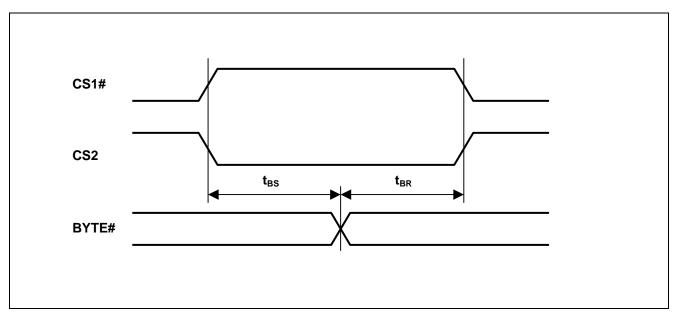


#### R1WV6416R Series

### BYTE# Timing Conditions

Parameter	Symbol	R1WV64	16R**-5S	R1WV6416R**-7S		Unit	Note
Falametei	Symbol	Min.	Max.	Min.	Max.	Onit	NOLE
Byte setup time	t <sub>BS</sub>	5	-	5	-	ms	
Byte recovery time	t <sub>BR</sub>	5	-	5	-	ms	

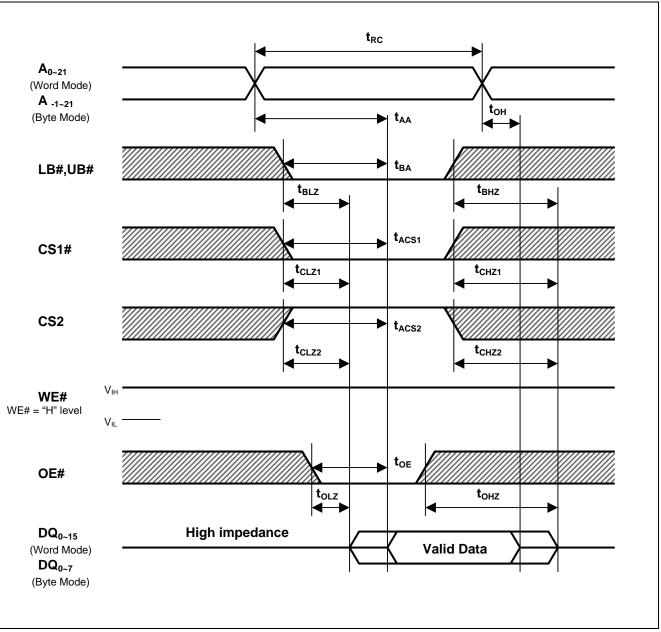
#### BYTE# Timing Waveforms





### **Timing Waveforms**

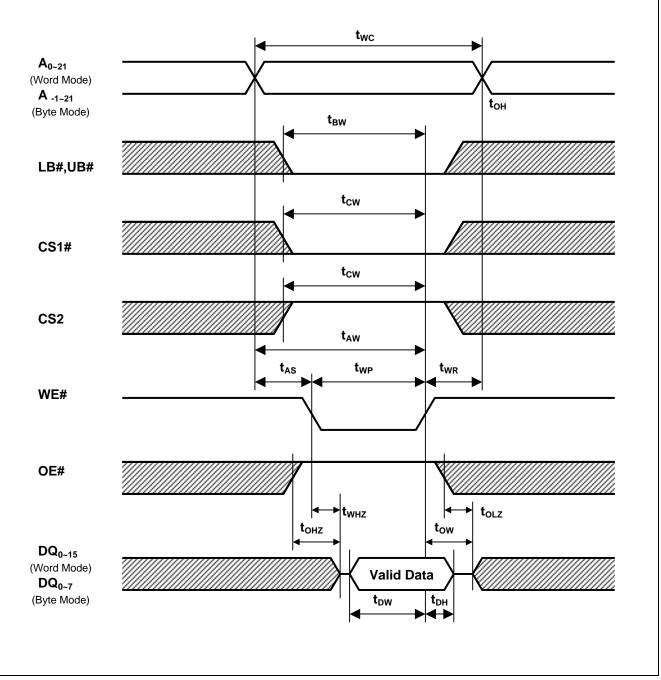
Read Cycle<sup>\*1</sup>



Note1. BYTE#  $\geq$  Vcc - 0.2V or BYTE#  $\leq$  0.2V



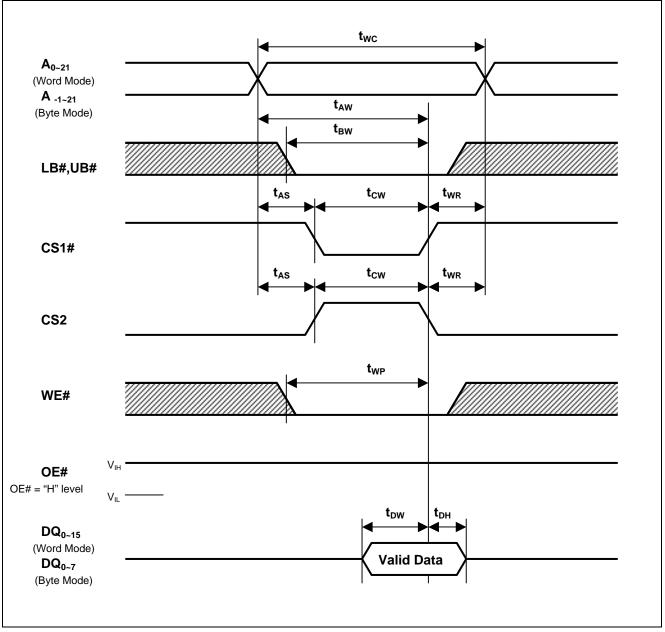
Write Cycle (1)<sup>\*1</sup> (WE# CLOCK)



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Note1. BYTE#  $\geq$  Vcc - 0.2V or BYTE#  $\leq$  0.2V

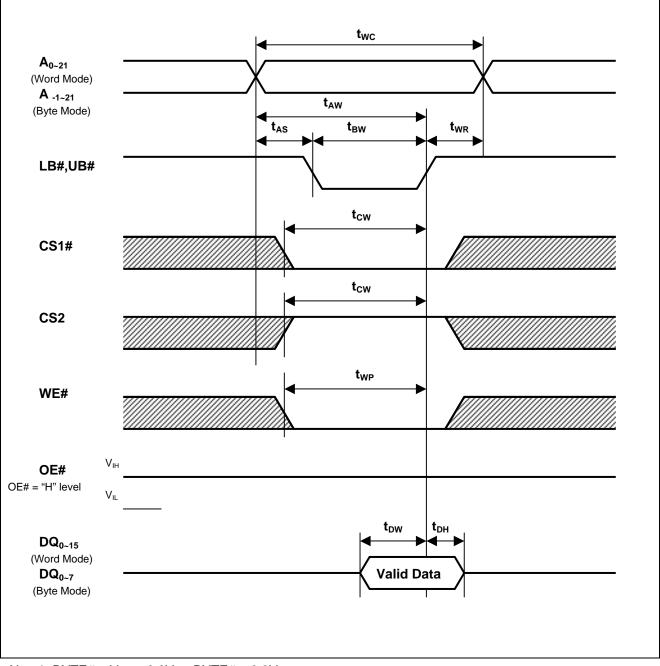
Write Cycle (2)<sup>\*1</sup> (CS1#, CS2 CLOCK)



Note1. BYTE#  $\geq$  Vcc - 0.2V or BYTE#  $\leq$  0.2V



Write Cycle (3)<sup>\*1</sup> (LB#, UB# CLOCK)



Note1. BYTE#  $\geq$  Vcc - 0.2V or BYTE#  $\leq$  0.2V



Parameter	Symbol	Min.	Тур	Max.	Unit	Test conditions <sup>*3,4</sup>		
$V_{\text{CC}}$ for data retention	V <sub>DR</sub>	2.0	-	3.6	V	Vin ≥ 0V BYTE# ≥ Vcc -0.2V or BYTE# ≤ 0.2V (1) 0V ≤ CS2 ≤ 0.2V or (2) CS1# ≥ V <sub>CC</sub> -0.2V, CS2 ≥ V <sub>CC</sub> -0.2V or (3) LB# = UB# ≥ V <sub>CC</sub> -0.2V, CS1# ≤ 0.2V, CS2 ≥ V <sub>CC</sub> -0.2V		
Data retention current	Iccdr	-	8 <sup>*1</sup>	24	μΑ	~+25°C	Vin ≥ 0V BYTE# ≥ Vcc -0.2V or	
		-	14 <sup>*2</sup>	48	μΑ	~+40°C	BYTE# $\leq 0.2V$ (1) 0V $\leq$ CS2 $\leq 0.2V$ or (2) CS1# $\geq V = 0.2V$	
		-	-	100	μΑ	~+70°C	(2) CS1# $\geq$ V <sub>CC</sub> -0.2V, CS2 $\geq$ V <sub>CC</sub> -0.2V or (3) LB# = UB# $\geq$ V <sub>CC</sub> -0.2V,	
		-	-	160	μΑ	~+85°C	$CS1\# \le 0.2V,$ $CS2 \ge V_{CC} - 0.2V$	
Chip select to data retention time	t <sub>CDR</sub>	0	-	-	ns	See retention waveform.		
Operation recovery time	t <sub>R</sub>	5	-	-	ms			

#### Low Vcc Data Retention Characteristics

Note 1. Typical parameter indicates the value for the center of distribution at 3.0V (Ta=  $25^{\circ}$ C), and not 100% tested.

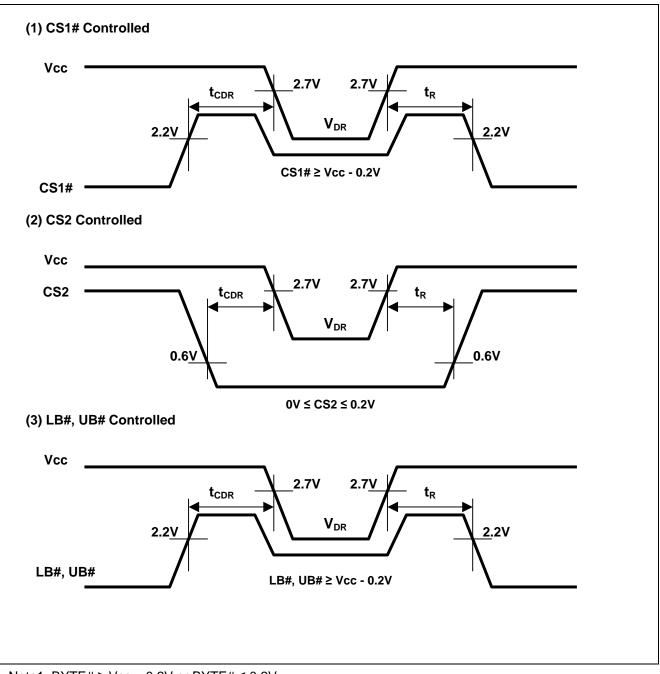
2. Typical parameter indicates the value for the center of distribution at 3.0V (Ta= 40°C), and not 100% tested.

3. BYTE# pin is supported for 48-pin TSOP (I) and 52-pin  $\mu\text{TSOP}$  (II) packages.

4. CS2 also controls address buffer, WE# buffer ,CS1# buffer ,OE# buffer ,LB# ,UB# buffer and Din buffer. If CS2 controls data retention mode, Vin levels (address, WE# ,OE#,CS1#,LB#,UB#,I/O) can be in the high impedance state. If CS1# controls data retention mode, CS2 must be CS2 ≥ Vcc-0.2V or0V ≤ CS2 ≤ 0.2V. The other input levels (address, WE# ,OE#,CS1#,LB#,UB#,I/O) can be in the high impedance state.



Low Vcc Data Retention Timing Waveforms<sup>\*1</sup>



#### Note1. BYTE# $\geq$ Vcc - 0.2V or BYTE# $\leq$ 0.2V



Revision History

### R1WV6416R Data Sheet

		Contents pf Revision				
Rev.	Date	Page	Description			
0.01	Mar.24, 2008	-	Initial issue: Preliminary Data Sheet			
1.00	May 07, 2009	-	Finalized			
		5	Operation Table corrected			
		6	Error corrected: I <sub>SB</sub> Test condition CS2=V <sub>IH</sub> ->V <sub>IL</sub>			

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## Old Company Name in Catalogs and Other Documents

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Renesas Electronics website: http://www.renesas.com

April 1<sup>st</sup>, 2010 Renesas Electronics Corporation

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